

## Silicon NPN Power Transistors

2SD725

## DESCRIPTION

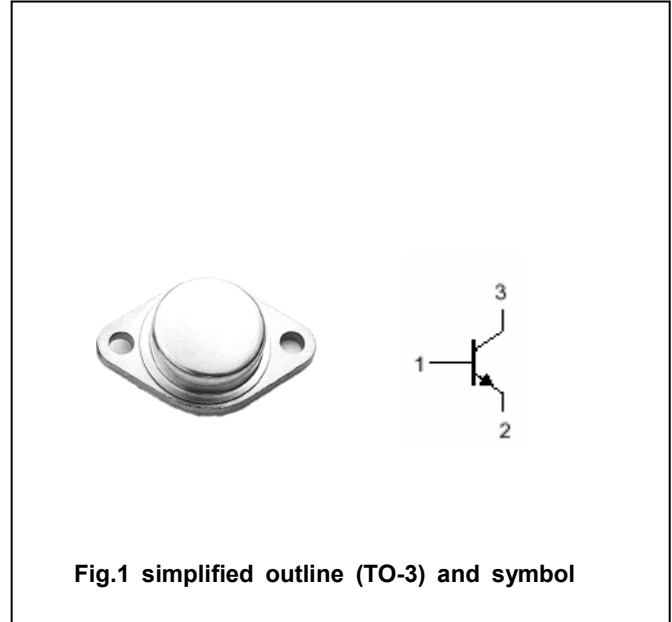
- With TO-3 package
- High voltage ,high speed
- Low collector saturation voltage

## APPLICATIONS

- For high voltage,power switching and TV horizontal output applications

## PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings( $T_a = \square$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	1500	V
$V_{CEO}$	Collector-emitter voltage	Open base	600	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		7	A
$P_C$	Collector power dissipation	$T_C = 25 \square$	50	W
$T_j$	Junction temperature		150	$\square$
$T_{stg}$	Storage temperature		-65~150	$\square$

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.1A; I <sub>B</sub> =0	600			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5 A; I <sub>B</sub> =1 A			5.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =5 A; I <sub>B</sub> =1 A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =800V; I <sub>E</sub> =0			10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			0.1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	8		36	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =5A ; V <sub>CE</sub> =5V	5			

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PACKAGE OUTLINE



Fig.2 Outline dimensions